Junichi Murota

List of Publications by Year
in descending order

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28 papers	722 citations	759233 12 h-index	552781 26 g-index
28 all docs	28 docs citations	28 times ranked	275 citing authors

#	Article	IF	Citations
1	Lowâ€temperature silicon selective deposition and epitaxy on silicon using the thermal decomposition of silane under ultraclean environment. Applied Physics Letters, 1989, 54, 1007-1009.	3.3	106
2	Selfâ€limited layerâ€byâ€layer etching of Si by alternated chlorine adsorption and Ar+ion irradiation. Applied Physics Letters, 1993, 63, 2803-2805.	3.3	101
3	Low-Temperature Epitaxial Growth ofSi/Si1-xGex/SiHeterostructure by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1994, 33, 2290-2299.	1.5	100
4	Atomically Controlled Processing for Group IV Semiconductors by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2006, 45, 6767-6785.	1.5	84
5	Boron Doping Effect on Silicon Film Deposition in the Si2â€‰Hâ€‰6â€‰â€â€‰â€‰Bâ€‰2â€‰Hâ€‰6â€‰â€â€‰He Gas Syst Electrochemical Society, 1986, 133, 1721-1724.	2.9	57
6	Selective Ge deposition on Si using thermal decomposition of GeH4. Applied Physics Letters, 1985, 47, 863-865.	3.3	47
7	Electronâ€cyclotronâ€resonance plasmaâ€enhanced chemical vapor deposition of epitaxial Si without substrate heating by ultraclean processing. Applied Physics Letters, 1991, 59, 2853-2855.	3.3	32
8	Deposition of Phosphorus Doped Silicon Films by Thermal Decomposition of Disilane. Japanese Journal of Applied Physics, 1984, 23, L493-L495.	1.5	30
9	Atomic layer processing for doping of SiGe. Thin Solid Films, 2006, 508, 279-283.	1.8	27
10	Atomic-layer adsorption of P on Si(100) and Ge(100) by PH3 using an ultraclean low-pressure chemical vapor deposition. Applied Surface Science, 2000, 162-163, 390-394.	6.1	25
11	Doping and electrical characteristics of in-situ heavily B-doped Si1â^'xâ^'yGexCy films epitaxially grown using ultraclean LPCVD. Thin Solid Films, 2000, 380, 57-60.	1.8	23
12	Doping and electrical characteristics of in situ heavily B-doped Si1â^'xGex films epitaxially grown using ultraclean LPCVD. Thin Solid Films, 1999, 343-344, 541-544.	1.8	15
13	Heavy B atomic-layer doping characteristics in Si epitaxial growth on B adsorbed Si(1 0 0) by ultraclean low-pressure CVD system. Solid-State Electronics, 2009, 53, 877-879.	1.4	11
14	Phosphorus Doping in Si1-x-yGexCyEpitaxial Growth by Low-Pressure Chemical Vapor Deposition Using a SiH4â€"GeH4â€"CH3SiH3â€"PH3â€"H2Gas System. Japanese Journal of Applied Physics, 2001, 40, 2697-2700.	1.5	9
15	Epitaxial growth of P atomic layer doped Si film by alternate surface reactions of PH3and Si2H6on strained Si1â^'xGex/Si(1â€‰0â€‰0) in ultraclean low-pressure CVD. Semiconductor Science and Technology, 2007, 22, S118-S122.	2.0	8
16	Heavy carbon atomic-layer doping at Si1â^'Ge /Si heterointerface. Thin Solid Films, 2010, 518, S222-S225.	1.8	8
17	Carbon effect on strain compensation in Si1â^'xâ^'yGexCy films epitaxially grown on Si(100). Thin Solid Films, 2006, 508, 140-142.	1.8	7
18	Arsenic atomic layer doping in Si using AsH3. Solid-State Electronics, 2015, 110, 29-34.	1.4	7

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19	Atomically Controlled Processing for Dopant Segregation in CVD Si and Ge Epitaxial Growth. ECS Journal of Solid State Science and Technology, 2018, 7, P305-P310.	1.8	5
20	W delta doping in Si(1 0 0) using ultraclean low-pressure CVD. Applied Surface Science, 2003, 212-213, 684-688.	6.1	4
21	Carbon doping effect on strain relaxation during Si1âˆ’xâˆ’yGexCy epitaxial growth on Si(1â€‰0â€‰0) at 500 Â°C. Semiconductor Science and Technology, 2007, 22, S5-S8.	2.0	4
22	Si epitaxial growth on self-limitedly B adsorbed Si1âˆ’Ge (100) by ultraclean low-pressure CVD system. Thin Solid Films, 2008, 517, 229-231.	1.8	4
23	Effect of carbon on the thermal stability of a Si atomic layer on Ge(1 0 0). Applied Surface Science, 2004, 224, 206-209.	6.1	3
24	Low-temperature reduction of Ge oxide by Si and SiH4 in low-pressure H2 and Ar environment. Solid-State Electronics, 2015, 110, 40-43.	1.4	2
25	Langmuir-Type Mechanism for In-Situ Doping in CVD Si and Si1âˆ’xGex Epitaxial Growth. ECS Journal of Solid State Science and Technology, 2021, 10, 024005.	1.8	2
26	Langmuir-Type Mechanism for In-Situ Doping in CVD Silicon-Germanium Epitaxial Growth. ECS Transactions, 2019, 90, 43-53.	0.5	1
27	Langmuir-Type Mechanism for In-Situ Boron Doping in CVD Si<inf>1-x</inf>Ge<inf>x</inf> Epitaxial Growth. , 2018, , .		0
28	Langmuir-Type Expressions for In-Situ Co-Doping of C with B or P in Si_{1â€“x}Ge_x Epitaxial Growth by Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2021, 10, 064004.	1.8	0